

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74VCX16374FT

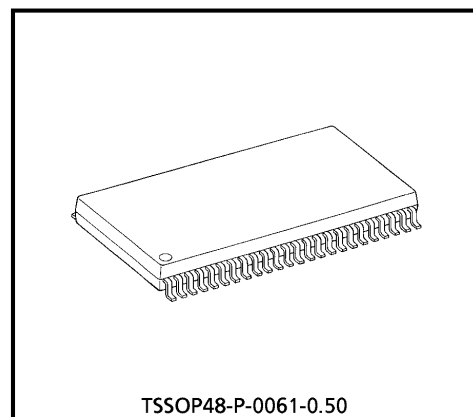
LOW-VOLTAGE 16-BIT D-TYPE FLIP-FLOP WITH 3.6V TOLERANT INPUTS AND OUTPUTS

The TC74VCX16374FT is a high performance CMOS 16-bit D-TYPE FLIP FLOP. Designed for use in 1.8, 2.5 or 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6V.

This 16-bit D-type flip-flop is controlled by a clock input (CK) and a output enable input (\overline{OE}) which are common to each byte. It can be used as two 8-bit flip-flops or one 16-bit flip-flop. When the \overline{OE} input is high, the outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge.



Weight : 0.25g (Typ.)

FEATURES

- Low Voltage Operation : $V_{CC} = 1.8 \sim 3.6V$
- High Speed Operation : $t_{pd} = 3.0ns$ (max.) at $V_{CC} = 3.0 \sim 3.6V$
 $t_{pd} = 3.9ns$ (max.) at $V_{CC} = 2.3 \sim 2.7V$
 $t_{pd} = 6.0ns$ (max.) at $V_{CC} = 1.8V$
- 3.6V Tolerant inputs and outputs.
- Output Current : $I_{OH}/I_{OL} = \pm 24mA$ (min.) at $V_{CC} = 3.0V$
 $I_{OH}/I_{OL} = \pm 18mA$ (min.) at $V_{CC} = 2.3V$
 $I_{OH}/I_{OL} = \pm 6mA$ (min.) at $V_{CC} = 1.8V$
- Latch-up Performance : $\pm 300mA$
- ESD Performance : Human Body Model $> \pm 2000V$
Machine Model $> \pm 200V$
- Package : TSSOP
(Thin Shrink Small Outline Package)
- Power Down Protection is provided on all inputs and outputs.
- Supports live insertion / withdrawal (Note 1)

(Note 1) To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

PIN CONNECTION

\overline{OE}	1	48	1CK
1Q1	2	47	1D1
1Q2	3	46	1D2
GND	4	45	GND
1Q3	5	44	1D3
1Q4	6	43	1D4
V_{CC}	7	42	V_{CC}
1Q5	8	41	1D5
1Q6	9	40	1D6
GND	10	39	GND
1Q7	11	38	1D7
1Q8	12	37	1D8
2Q1	13	36	2D1
2Q2	14	35	2D2
GND	15	34	GND
2Q3	16	33	2D3
2Q4	17	32	2D4
V_{CC}	18	31	V_{CC}
2Q5	19	30	2D5
2Q6	20	29	2D6
GND	21	28	GND
2Q7	22	27	2D7
2Q8	23	26	2D8
2OE	24	25	2CK

(TOP VIEW)

980508EBA2

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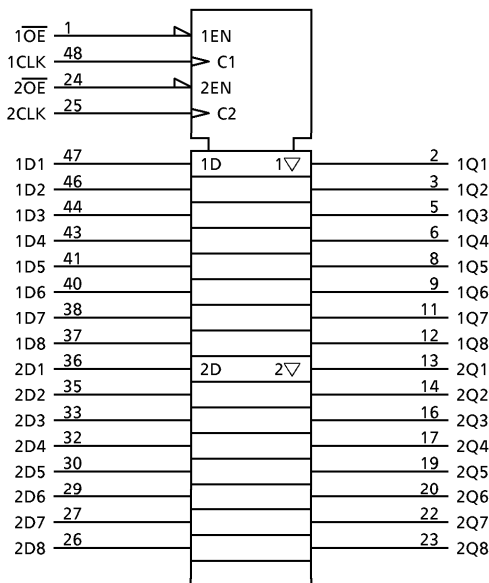
TRUTH TABLE

INPUT			OUTPUT
1OE	1CK	1D1-1D8	1Q1-1Q8
H	X	X	Z
L	\downarrow	X	Qn
L	\uparrow	L	L
L	\uparrow	H	H

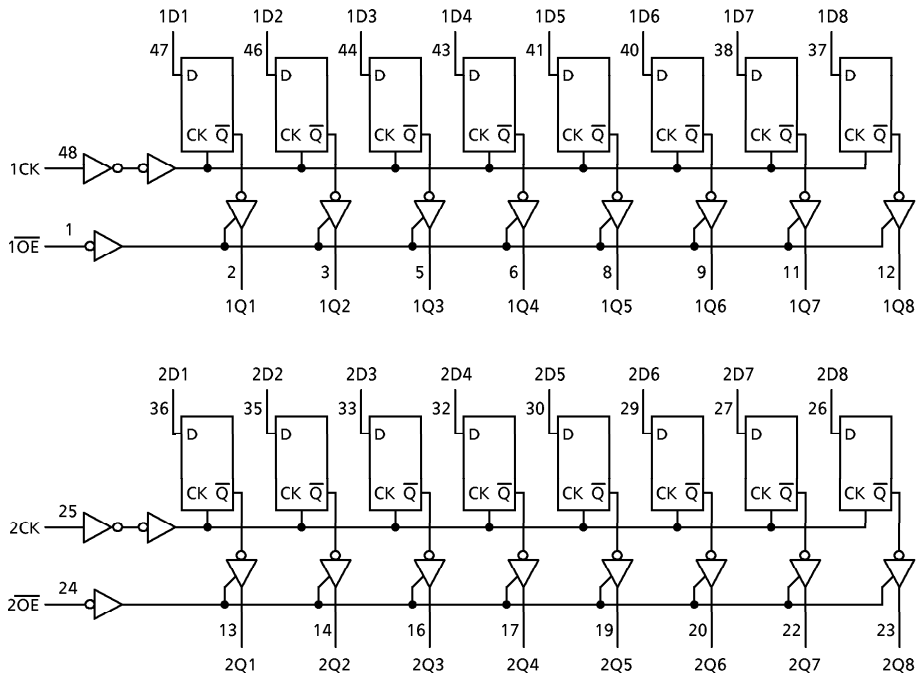
INPUT			OUTPUT
2OE	2CK	2D1-2D8	2Q1-2Q8
H	X	X	Z
L	\downarrow	X	Qn
L	\uparrow	L	L
L	\uparrow	H	H

X : Don't Care
 Z : High impedance
 Qn : No change

IEC LOGIC SYMBOL



SYSTEM DIAGRAM



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MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Power Supply Voltage	V_{CC}	-0.5~4.6	V
DC Input Voltage	V_{IN}	-0.5~4.6	V
DC Output Voltage	V_{OUT}	-0.5~4.6 (Note 1)	V
		-0.5~ V_{CC} +0.5 (Note 2)	
Input Diode Current	I_{IK}	-50	mA
Output Diode Current	I_{OK}	±50 (Note 3)	mA
DC Output Current	I_{OUT}	±50	mA
Power Dissipation	P_D	400	mW
DC V_{CC} / Ground Current Per Supply Pin	I_{CC}/I_{GND}	±100	mA
Storage Temperature	T_{stg}	-65~150	°C

(Note 1) Off-State

(Note 2) High or Low State. I_{OUT} absolute maximum rating must be observed.

(Note 3) $V_{OUT} < GND$, $V_{OUT} > V_{CC}$

RECOMMENDED OPERATING RANGE

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	1.8~3.6	V
		1.2~3.6 (Note 4)	
Input Voltage	V_{IN}	-0.3~3.6	V
Output Voltage	V_{OUT}	0~3.6 (Note 5)	V
		0~ V_{CC} (Note 6)	
Output Current	I_{OH}/I_{OL}	±24 (Note 7)	mA
		±18 (Note 8)	
		±6 (Note 9)	
Operating Temperature	T_{opr}	-40~85	°C
Input Rise And Fall Time	dt/dv	0~10 (Note 10)	ns/V

(Note 4) Data Retention Only

(Note 5) Off-State

(Note 6) High or Low State

(Note 7) $V_{CC} = 3.0\sim 3.6V$

(Note 8) $V_{CC} = 2.3\sim 2.7V$

(Note 9) $V_{CC} = 1.8V$

(Note 10) $V_{IN} = 0.8\sim 2.0V$, $V_{CC} = 3.0V$

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C, 2.7V < VCC ≤ 3.6V)

PARAMETER		SYMBOL	TEST CONDITION		VCC (V)	MIN.	MAX.	UNIT
Input Voltage	"H" Level	V _{IH}			2.7~3.6	2.0	—	V
	"L" Level	V _{IL}			2.7~3.6	—	0.8	
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100μA	2.7~3.6	V _{CC} - 0.2	—	V
				I _{OH} = -12mA	2.7	2.2	—	
				I _{OH} = -18mA	3.0	2.4	—	
				I _{OH} = -24mA	3.0	2.2	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100μA	2.7~3.6	—	0.2	
				I _{OL} = 12mA	2.7	—	0.4	
				I _{OL} = 18mA	3.0	—	0.4	
				I _{OL} = 24mA	3.0	—	0.55	
Input Leakage Current		I _{IN}	V _{IN} = 0~3.6V		2.7~3.6	—	± 5.0	μA
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6V		2.7~3.6	—	± 10.0	μA
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6V		0	—	10.0	μA
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND		2.7~3.6	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6V		2.7~3.6	—	± 20.0	
Increase In I _{CC} Per Input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6V		2.7~3.6	—	750	μA

ELECTRICAL CHARACTERISTICS

DC characteristics ($T_a = -40 \sim 85^\circ\text{C}$, $2.3\text{V} \leq V_{CC} \leq 2.7\text{V}$)

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	MIN.	MAX.	UNIT
Input Voltage	"H" Level	V_{IH}			2.3~2.7	1.6	—	V
	"L" Level	V_{IL}			2.3~2.7	—	0.7	
Output Voltage	"H" Level	V_{OH}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -100\mu\text{A}$	2.3~2.7	$V_{CC} - 0.2$	—	V
				$I_{OH} = -6\text{mA}$	2.3	2.0	—	
				$I_{OH} = -12\text{mA}$	2.3	1.8	—	
				$I_{OH} = -18\text{mA}$	2.3	1.7	—	
	"L" Level	V_{OL}	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 100\mu\text{A}$	2.3~2.7	—	0.2	
				$I_{OL} = 12\text{mA}$	2.3	—	0.4	
			$I_{OL} = 18\text{mA}$	2.3	—	0.6		
Input Leakage Current		I_{IN}	$V_{IN} = 0 \sim 3.6\text{V}$		2.3~2.7	—	± 5.0	μA
3-State Output Off-State Current		I_{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0 \sim 3.6\text{V}$		2.3~2.7	—	± 10.0	μA
Power Off Leakage Current		I_{OFF}	$V_{IN}, V_{OUT} = 0 \sim 3.6\text{V}$		0	—	10.0	μA
Quiescent Supply Current		I_{CC}	$V_{IN} = V_{CC} \text{ or } \text{GND}$		2.3~2.7	—	20.0	μA
			$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6V_{CC}$		2.3~2.7	—	± 20.0	

ELECTRICAL CHARACTERISTICS

DC characteristics (Ta = -40~85°C, 1.8V ≤ VCC < 2.3V)

PARAMETER		SYMBOL	TEST CONDITION		VCC (V)	MIN.	MAX.	UNIT
Input Voltage	"H" Level	V _{IH}			1.8~2.3	0.7 × V _{CC}	—	V
	"L" Level	V _{IL}			1.8~2.3	—	0.2 × V _{CC}	
Output Voltage	"H" Level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100μA	1.8	V _{CC} - 0.2	—	V
				I _{OH} = -6mA	1.8	1.4	—	
	"L" Level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100μA	1.8	—	0.2	
				I _{OL} = 6mA	1.8	—	0.3	
Input Leakage Current		I _{IN}	V _{IN} = 0~3.6V		1.8	—	± 5.0	μA
3-State Output Off-State Current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0~3.6V		1.8	—	± 10.0	μA
Power Off Leakage Current		I _{OFF}	V _{IN} , V _{OUT} = 0~3.6V		0	—	10.0	μA
Quiescent Supply Current		I _{CC}	V _{IN} = V _{CC} or GND		1.8	—	20.0	μA
			V _{CC} ≤ (V _{IN} , V _{OUT}) ≤ 3.6V		1.8	—	± 20.0	

AC characteristics (Ta = -40~85°C, Input $t_r = t_f = 2.0\text{ns}$, $C_L = 30\text{pF}$, $R_L = 500\Omega$)

PARAMETER	SYMBOL	TEST CONDITION	V _{CC} (V)	MIN.	MAX.	UNIT
Maximam Clock Frequency	f _{MAX}	(Fig.1, 2)	1.8	125	—	MHz
			2.5 ± 0.2	200	—	
			3.3 ± 0.3	250	—	
Propagation Delay Time (CK-Q)	t _{pLH} t _{pHL}	(Fig.1, 2)	1.8	1.5	6.0	ns
			2.5 ± 0.2	1.0	3.9	
			3.3 ± 0.3	0.8	3.0	
3-State Output Enable Time	t _{pZL} t _{pZH}	(Fig.1, 3)	1.8	1.5	7.0	ns
			2.5 ± 0.2	1.0	4.6	
			3.3 ± 0.3	0.8	3.5	
3-State Output Disable Time	t _{pLZ} t _{pHZ}	(Fig.1, 3)	1.8	1.5	5.0	ns
			2.5 ± 0.2	1.0	3.8	
			3.3 ± 0.3	0.8	3.5	
Minimum Pulse Width (CK)	t _w (H) t _w (L)	(Fig.1, 2)	1.8	3.0	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum Set-up Time	t _s	(Fig.1, 2)	1.8	2.5	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum Hold Time	t _h	(Fig.1, 2)	1.8	1.0	—	ns
			2.5 ± 0.2	1.0	—	
			3.3 ± 0.3	1.0	—	
Output To Output Skew	t _{osLH} t _{osHL}	(Note 11)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

For C_L = 50pF, add approximately 300ps to the AC maximum specification.

(Note 11) Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic switching characteristics (Ta = 25°C, Input tr = tf = 2.0ns, CL = 30pF)

PARAMETER	SYMBOL	TEST CONDITION	VCC (V)	TYP.	UNIT
Quiet Output Maximum Dynamic VOL	VOLP	VIH = 1.8V, VIL = 0V (Note 12)	1.8	0.25	V
		VIH = 2.5V, VIL = 0V (Note 12)	2.5	0.6	
		VIH = 3.3V, VIL = 0V (Note 12)	3.3	0.8	
Quiet Output Minimum Dynamic VOL	VOLV	VIH = 1.8V, VIL = 0V (Note 12)	1.8	-0.25	V
		VIH = 2.5V, VIL = 0V (Note 12)	2.5	-0.6	
		VIH = 3.3V, VIL = 0V (Note 12)	3.3	-0.8	
Quiet Output Minimum Dynamic VOH	VOHV	VIH = 1.8V, VIL = 0V (Note 12)	1.8	1.5	V
		VIH = 2.5V, VIL = 0V (Note 12)	2.5	1.9	
		VIH = 3.3V, VIL = 0V (Note 12)	3.3	2.2	

(Note 12) Parameter guaranteed by design.

Capacitive characteristics (Ta = 25°C)

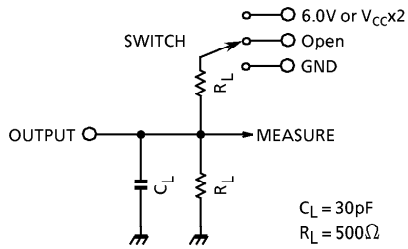
PARAMETER	SYMBOL	TEST CONDITION	VCC (V)	TYP.	UNIT
Input Capacitance	CIN		1.8, 2.5, 3.3	6	pF
Output Capacitance	CO		1.8, 2.5, 3.3	7	pF
Power Dissipation Capacitance	CPD	fIN = 10MHz (Note 13)	1.8, 2.5, 3.3	20	pF

(Note 13) CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC (opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 16 \text{ (per bit)}$$

Fig.1 Test circuit



PARAMETER	SWITCH
t_{pLH} , t_{pHL}	Open
t_{pLZ} , t_{pZL}	6.0V @ $V_{CC} = 3.3 \pm 0.3\text{V}$ $V_{CC} \times 2$ @ $V_{CC} = 2.5 \pm 0.2\text{V}$ @ $V_{CC} = 1.8\text{V}$
t_{pHZ} , t_{pZH}	GND

AC WAVEFORM

Fig.2 t_{pLH} , t_{pHL} , t_w , t_s , t_h

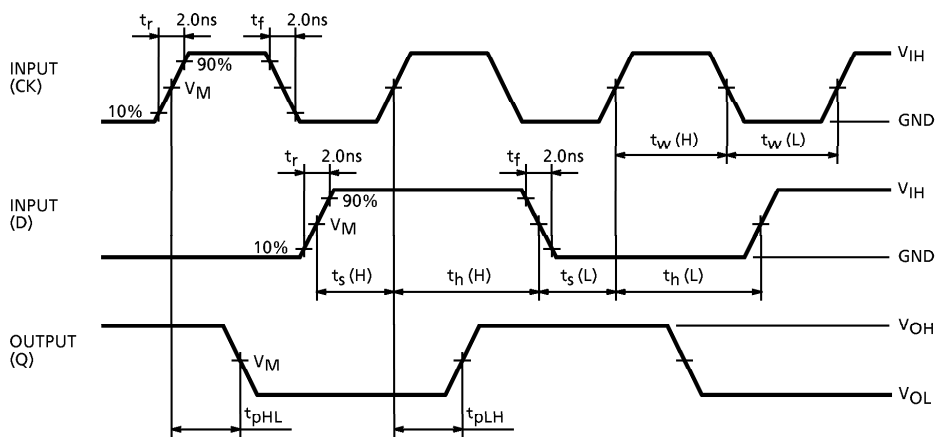
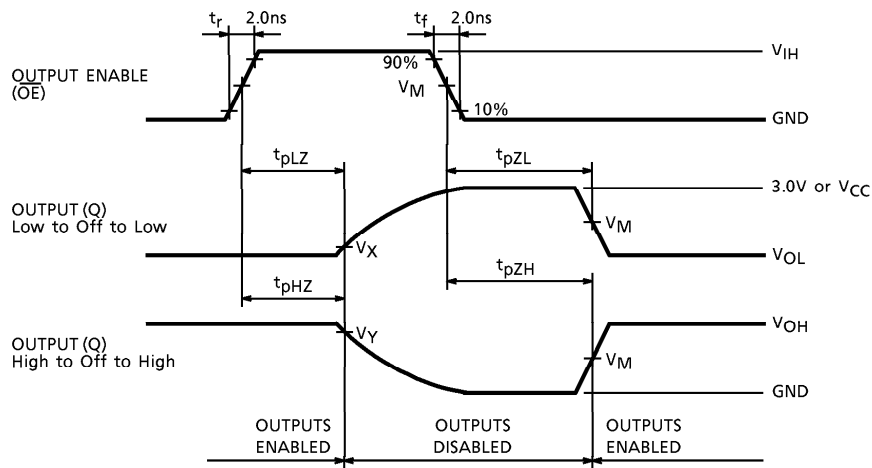


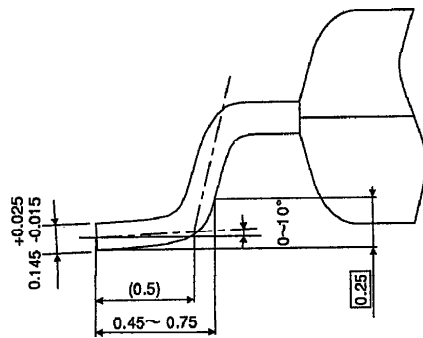
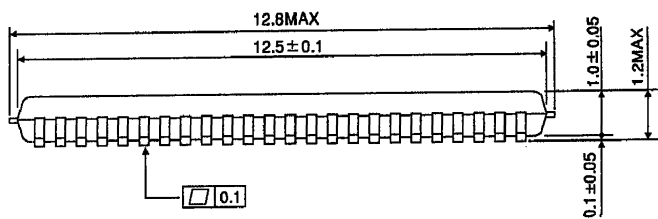
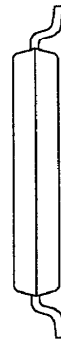
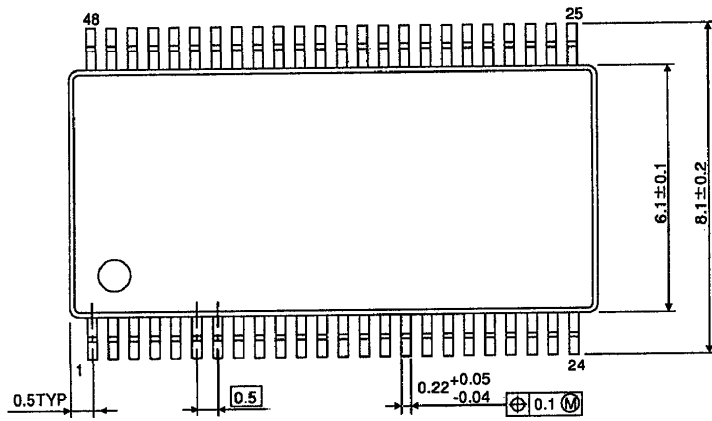
Fig.3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}



SYMBOL	V_{CC}		
	$3.3 \pm 0.3V$	$2.5 \pm 0.2V$	1.8V
V_{IH}	2.7V	V_{CC}	V_{CC}
V_M	1.5V	$V_{CC} / 2$	$V_{CC} / 2$
V_X	$V_{OL} + 0.3V$	$V_{OL} + 0.15V$	$V_{OL} + 0.15V$
V_Y	$V_{OH} - 0.3V$	$V_{OH} - 0.15V$	$V_{OH} - 0.15V$

OUTLINE DRAWING
TSSOP48-P-0061-0.50

Unit : mm



Weight : 0.25g (Typ.)